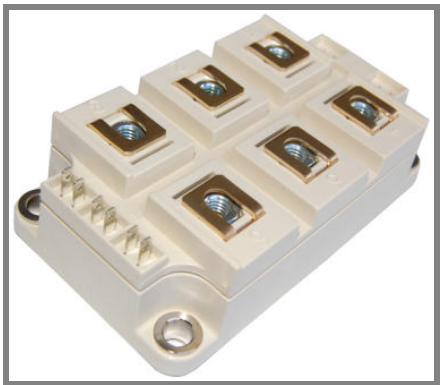
SKM 200 GARL 066 T



SEMITRANS® 5

Trench IGBT Modules

SKM 200 GARL 066 T

Target Data

Features

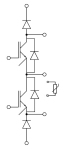
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- Integrated NTC temperature sensor

Typical Applications

- UPS
- INVERTER

Remarks

- Case temperature limited to T_c =125°C max, recommended T_{op} = -40..+150°C

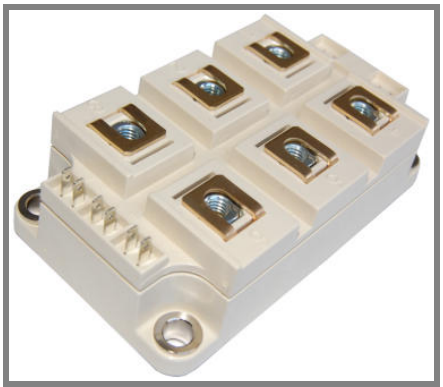


GARL-T

Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified			
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		600	V
I_C	T_j = 175 °C	T_c = 25 °C	280	A
		T_c = 80 °C	210	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		400	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 360 V; $V_{GE} \leq$ 15 V; V_{CES} < 600 V	T_j = 150 °C	6	µs
Inverse Diode				
I_F	T_j = 175 °C	T_c = 25 °C	27	A
		T_c = 80 °C	20	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		40	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	95	A
Freewheeling Diode				
I_F	T_j = 175 °C	T_c = 25 °C	280	A
		T_c = 80 °C	200	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		400	A
I_{FSM}	t_p = 10 ms; half sine wave	T_j = 150 °C	1620	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40 ... + 175	°C
T_{stg}			- 40 ... + 125	°C
V_{isol}	AC, 1 min.		2500	V

Characteristics	T_{case} = 25°C, unless otherwise specified					
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 3,2 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C			0,01	mA
I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V	T_j = 25 °C			1200	nA
V_{CE0}		T_j = 25 °C		0,9	1	V
		T_j = 150 °C		0,7	0,8	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		2,7	4,5	mΩ
		T_j = 150°C		5	6,5	mΩ
$V_{CE(sat)}$	I_{Cnom} = 200 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,45	1,9	V
		T_j = 150°C$_{chiplev.}$		1,7	2,1	V
C_{ies}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		12,3		nF
C_{oes}				0,76		nF
C_{res}				0,36		nF
R_{Gint}	T_j = °C			1		Ω
$t_{d(on)}$	R_{Gon} = 2,4 Ω	V_{CC} = 300V, I_C= 200A, T_j = 150 °C, V_{GE} = -8V/+15V				ns
t_r						ns
E_{on}						mJ
$t_{d(off)}$	R_{Goff} = 2,4 Ω					ns
t_f						ns
E_{off}						mJ
$R_{th(j-c)}$	per IGBT			0,21		K/W

SKM 200 GARL 066 T



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Features

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Typical Applications

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- INVERTER

Remarks

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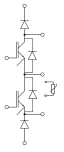
Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse Diode						
$V_F = V_{EC}$	I_{Fnom} = 20 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,45	1,7	V
		T_j = 150 °$C_{chiplev.}$		1,45	1,7	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 150 °C		0,9	1	V
r_F		T_j = 25 °C		22,5	30	mΩ
		T_j = 150 °C		27,5	35	mΩ
I_{RRM}	I_F = 20 A	T_j = 150 °C				A
Q_{rr}						µC
E_{rr}	V_{GE} = -8 V; V_{CC} = 300 V					mJ
$R_{th(j-c)D}$	per diode			3		K/W
Free-wheeling diode						
$V_F = V_{EC}$	I_{Fnom} = 200 A; V_{GE} = 0 V	T_j = 25 °$C_{chiplev.}$		1,4	1,6	V
		T_j = 150 °$C_{chiplev.}$		1,3	1,45	V
V_{F0}		T_j = 25 °C		0,95	1	V
		T_j = 150 °C		0,85	0,9	V
r_F		T_j = 25 °C		2,2	3	V
		T_j = 150 °C		2,1	2,7	V
I_{RRM}	I_F = 200 A	T_j = 150 °C				A
Q_{rr}						µC
E_{rr}	V_{GE} = 0 V; V_{CC} = 600 V					mJ
$R_{th(j-c)FD}$	per diode			0,37		K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6		2,5		5	Nm
w					310	g
Temperature sensor						
R_{100}	T_s=100°C (R_{25}=5kΩ)			493±5%		Ω
						K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.



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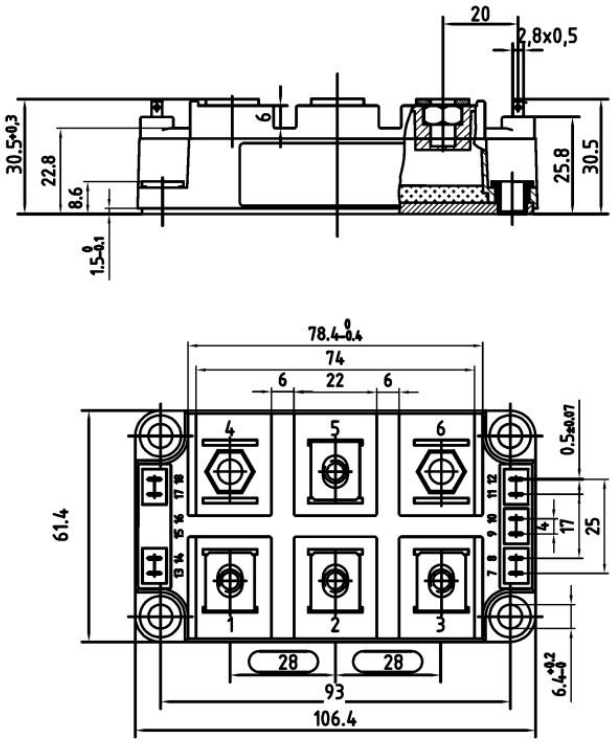
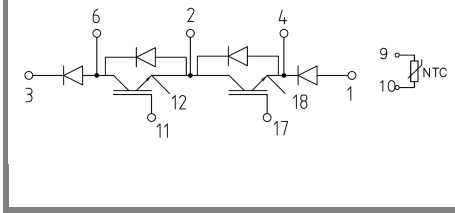


Case D61



GARL-T Case D61

